IN THE CLAIMS:

Please cancel claims 3-5, 21, 22, 24, 27 and 28 in their entirety without prejudice nor disclaimer of the subject matter set forth therein.

1. (Previously Presented) A semiconductor device comprising:

a lower electrode formed on a substrate;

a capacitive insulating film made of a ferroelectric film on the lower electrode;

an upper electrode formed on the capacitive insulating film;

a contact layer formed directly on the upper electrode so as not to be in contact with the capacitive insulating film;

an insulating film made of silicon dioxide or nitride formed directly on the contact layer to cover the lower electrode, the capacitive insulating film, the upper electrode and the contact layer, and

wherein the contact layer is provided on a surface of the upper electrode and in a region other than the region where a metal interconnect is connected to the upper electrode, and

wherein the contact layer is a single layer film or a multilayer structure, the single-layer film being made of a metal oxide or a metal nitride, the multilayer structure being made up of metal oxide and metal nitride films.

2. (Cancelled).

3.-9. (Canceled)

10. (Previously Presented) The device of Claim 1,

wherein the metal oxide film is made of an oxide of Ti or an oxide of Ta, while the metal nitride film is made of a nitride of Ti or a nitride of Ta.

11-12. (Cancelled).

13. (Previously presented) The device of Claim 1, wherein the ferroelectric film includes $SrBi_2Ta_2O_9$.

14. (Previously presented) The device of Claim 1, wherein the insulating film is unlikely to peel off due to the contact layer.

15. (Previously presented) The device of Claim 1, wherein the contact layer is made from metal atoms which are unlikely to diffuse into the upper electrode.

16. (Canceled)

17. (Previously Presented) The device of Claim 1, wherein a portion of the upper surface of the upper electrode is not covered by the contact layer and connected to the metal interconnect.

18. (Previously Presented) A semiconductor device comprising:

a lower electrode formed on a substrate;

a capacitive insulating film made of a ferroelectric film on the lower electrode;

an upper electrode formed on the capacitive insulating film;

a contact layer formed directly on the upper electrode so as to be in no contact with the capacitive insulating film, and

an insulating film made of silicon dioxide or nitride formed directly on the contact layer to cover the lower electrode, the capacitive insulating film, the upper electrode and the contact layer,

wherein a portion of the upper surface of the upper electrode is not covered by the contact layer and connected to a metal interconnect, and

wherein the contact layer is a single-layer film or a multilayer structure, the single-layer film being made of a metal oxide or a metal nitride, the multilayer structure being made up of metal oxide and metal nitride films.

19. (Previously Presented) The device of Claim 18, wherein the metal oxide film is made of an oxide of Ti or an oxide of Ta, while the metal nitride film is made of a nitride of Ti or a nitride of Ta.

20.-22 (Canceled)

23. (Previously Presented) A semiconductor device comprising:

a lower electrode formed on a substrate;

a capacitive insulating film made of a ferroelectric film on the lower electrode,

an upper electrode formed on the capacitive insulating film; and

a contact layer formed directly on the upper electrode so as to be in no contact with the capacitive insulating film,

wherein the entire upper surface of the upper electrode is in no contact with an insulating film, and

wherein the contact layer is made from TaO or TaN.

24. (Canceled)

25. (Previously Presented) The device of Claim 1, wherein a portion of the upper surface of the capacitive insulating film is covered by the insulating film.

26. (Previously Presented) The device of Claim 18, wherein a portion of the upper surface of the capacitive insulating film is covered by the insulating film.

27.-28 (Canceled)